

WHAT IS CLAIMED IS:

1. A method for manufacturing a resist pattern, comprising the step of forming the resist pattern by discharging a composition containing a photosensitizer  
5 on an object to be processed under reduced pressure.

2. A method for manufacturing a resist pattern according to claim 1, wherein the composition containing the photosensitizer is made by dissolving or by dispersing the photosensitizer into a solvent.  
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3. A manufacturing method of a resist pattern according to claim 1, wherein said semiconductor device is incorporated into at least one selected from the group consisting of a display device, a personal computer and a portable image reproduction device.  
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4. A method for manufacturing a semiconductor device, comprising the steps of:  
forming a resist pattern by discharging a composition containing a photosensitizer on an object to be processed under reduced pressure; and  
20 etching the object to be processed by using the resist pattern as a mask.

5. A method for manufacturing a semiconductor device according to claim 4, wherein the composition containing the photosensitizer is made by dissolving or by dispersing the photosensitizer into a solvent.  
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6. A manufacturing method of a semiconductor device according to claim 4, wherein said semiconductor device is incorporated into at least one selected from the group consisting of a display device, a personal computer and a portable image reproduction device.  
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7. A method for manufacturing a semiconductor device, comprising the steps of:

forming a resist pattern by discharging a composition containing a photosensitizer on an object to be processed under reduced pressure;

5 irradiating the resist pattern through a photomask with light within a photosensitive wavelength region of the photosensitizer;

etching the object to be processed by using the resist pattern as a mask; and

removing the resist pattern on the object to be processed.

10 8. A method for manufacturing a semiconductor device according to claim 7, wherein the composition containing the photosensitizer is made by dissolving or by dispersing the photosensitizer into a solvent.

15 9. A manufacturing method of a semiconductor device according to claim 7, wherein said semiconductor device is incorporated into at least one selected from the group consisting of a display device, a personal computer and a portable image reproduction device.

20 10. A method for manufacturing a semiconductor device, comprising the steps of:

forming a conductive layer by discharging a composition containing a conductive material;

forming a resist pattern by discharging the composition containing a photosensitizer on the conductive layer under reduced pressure;

25 irradiating the resist pattern through a photomask with light within a photosensitive wavelength region of the photosensitizer;

etching the conductive layer by using the resist pattern as a mask; and

removing the resist pattern on the conductive layer.

30 11. A method for manufacturing a semiconductor device according to claim

10, wherein the composition containing the photosensitizer is made by dissolving or by dispersing the photosensitizer into a solvent.

12. A manufacturing method of a semiconductor device according to claim 5 10, wherein said semiconductor device is incorporated into at least one selected from the group consisting of a display device, a personal computer and a portable image reproduction device.

13. A method of manufacturing a semiconductor device comprising:  
10 forming a resist pattern by discharging a composition containing a photosensitizer on a first conductive layer under reduced pressure;  
irradiating the resist pattern through a photomask with light within a photosensitive wavelength region of the photosensitizer;  
etching the first conductive layer by using the resist pattern as a mask to  
15 form a plurality of gate wirings and a plurality of gate electrodes over a substrate;  
removing the resist pattern on the first conductive layer;  
forming an insulating film over the plurality of gate wirings;  
forming a plurality of semiconductor islands over the gate electrodes with said insulating film interposed therebetween;  
20 forming a resist pattern by discharging a composition containing a photosensitizer on a second conductive layer under reduced pressure;  
irradiating the resist pattern through a photomask with light within a photosensitive wavelength region of the photosensitizer;  
etching the second conductive layer by using the resist pattern as a mask to  
25 form a plurality of pixel electrodes arranged in a matrix form over the substrate;  
removing the resist pattern on the second conductive layer;  
forming a resist pattern by discharging a composition containing a photosensitizer on a third conductive layer under reduced pressure;  
irradiating the resist pattern through a photomask with light within a  
30 photosensitive wavelength region of the photosensitizer;

etching the third conductive layer by using the resist pattern as a mask to form a plurality of source wirings wherein said plurality of source wirings extend across said plurality of gate wirings; and

removing the resist pattern on the third conductive layer.

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14. A method of manufacturing a semiconductor device according to claim 13, wherein the composition containing the photosensitizer is made by dissolving or by dispersing the photosensitizer into a solvent.

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15. A method of manufacturing a semiconductor device according to claim 13, wherein said semiconductor device is incorporated into at least one selected from the group consisting of a display device, a personal computer and a portable image reproduction device.

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16. A method of manufacturing a semiconductor device comprising:

forming a resist pattern by discharging a composition containing a photosensitizer on a first conductive layer under reduced pressure;

irradiating the resist pattern through a photomask with light within a photosensitive wavelength region of the photosensitizer;

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etching the first conductive layer by using the resist pattern as a mask to form a plurality of gate wirings and a plurality of gate electrodes over a substrate;

removing the resist pattern on the first conductive layer;

forming an insulating film over the plurality of gate wirings;

forming a plurality of first semiconductor islands over the gate electrodes

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with said insulating film interposed therebetween;

forming each of a plurality of channel protective layers over each of the plurality of first semiconductor islands;

forming a plurality of second semiconductor islands over the plurality of first semiconductor islands with the plurality of channel protective layers interposed

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therebetween;

forming a resist pattern by discharging a composition containing a photosensitizer on a second conductive layer under reduced pressure;

irradiating the resist pattern through a photomask with light within a photosensitive wavelength region of the photosensitizer;

5 etching the second conductive layer by using the resist pattern as a mask to form a plurality of pixel electrodes arranged in a matrix form over the substrate;

removing the resist pattern on the second conductive layer;

forming a resist pattern by discharging a composition containing a photosensitizer on a third conductive layer under reduced pressure;

10 irradiating the resist pattern through a photomask with light within a photosensitive wavelength region of the photosensitizer;

etching the third conductive layer by using the resist pattern as a mask to form a plurality of source wirings wherein said plurality of source wirings extend across said plurality of gate wirings; and

15 removing the resist pattern on the third conductive layer.

17. A method of manufacturing a semiconductor device according to claim 16, wherein the composition containing the photosensitizer is made by dissolving or by dispersing the photosensitizer into a solvent.

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18. A method of manufacturing a semiconductor device according to claim 16, wherein said semiconductor device is incorporated into at least one selected from the group consisting of a display device, a personal computer and a portable image reproduction device.

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